ELSEVIER

Surface Science 406 (1998) 329–331

surface science

# Author index

Allouche, A., Water adsorption on NaCl(100): a quantum ab-initio cluster calculation 406 (1998) 279
Andreazza-Vignolle, C., see Brault 406 (1998) L597
Asmussen, B., M. Strzelczyk, W. Press and J.Z. Larese, Low coverage structure of tetramethyltin adsorbed on graphite 406 (1998) 138
Atrei, A., see Ceelen 406 (1998) 264
Averous, M., see Breton 406 (1998) 63

Baddeley, C., see Gießel 406 (1998) 90
Balzarotti, A., see Motta 406 (1998) 254
Bao, S., see Gießel 406 (1998) 90
Barbier, A., Generalized model for interface description 406 (1998) 69
Bardi, U., see Ceelen 406 (1998) 264
Bartelt, M.C., see Zhang 406 (1998) 178
Benedek, G., A. Glebov, W. Silvestri, J.G. Skofronick and J.P. Toennies, Reply to M.C. Vargas and W.L. Mochán's Comment on "Evidence for a deep bound-state level in the $^4$He–NaCl(001) potential" 406 (1998) L621
Bernasek, S.L., see Dooley 406 (1998) 206
Berndt, W., see Gießel 406 (1998) 90
Borisov, A.G., see Hecht 406 (1998) L607
Bradshaw, A.M., see Gießel 406 (1998) 90
Brault, P., A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597
Breton, G., M. Nouaoura, C. Gautier, M. Cambon, S. Charar, M. Averous and V. Ribes, Annealing under vacuum and Se flux of $CaF_2$ molecular beam epitaxy surfaces prior to PbSe/$CaF_2$/Si growth 406 (1998) 63
Brongersma, H.H., see Ceelen 406 (1998) 264

Cai, W.B., B. Ren, X.Q. Li, C.X. She, F.M. Liu, X.W. Cai and Z.Q. Tian, Investigation of surface-enhanced Raman scattering from platinum electrodes using a confocal Raman microscope: dependence of surface roughening pretreatment 406 (1998) 9
Cai, X.W., see Cai 406 (1998) 9
Calarco, R., see Motta 406 (1998) 254
Cambon, M., see Breton 406 (1998) 63
Campbell, C.T., see Yoshihara 406 (1998) 235
Campbell, J.M., see Yoshihara 406 (1998) 235
Carley, A.F., P.R. Davies, M.W. Roberts, A.K. Santra and K.K. Thomas, Coadsorption of carbon monoxide and nitric oxide at Ag(111): evidence for a CO–NO surface complex 406 (1998) L587
Carlsson, A., L.R. Wallenberg, C. Persson and W. Seifert, Strain state in semiconductor quantum dots on surfaces: a comparison of electron microscopy and finite element calculations 406 (1998) 48
Castro Cal, J., see Motta 406 (1998) 254
Ceelen, W.C.A.N., A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264
Chang, C.-H., see Chen 406 (1998) 167
Charar, S., see Breton 406 (1998) 63
Chen, C.-T., J.-R. Maa, Y.-M. Yang and C.-H. Chang, Effects of electrolytes and polarity of organic liquids on the coalescence of droplets at aqueous-organic interfaces 406 (1998) 167
Choutov, D.A., see Winningham 406 (1998) 221

Davies, P.R., see Carley 406 (1998) L587
De Crescenzi, M., see Motta 406 (1998) 254
Denier van der Gon, A.W., see Ceelen 406 (1998) 264
Dooley, P. and S.L. Bernasek, Pooling analysis of scanning probe microscopy images 406 (1998) 206
Douglas, K., see Winningham 406 (1998) 221

Eggeling, J., see Mulcahy 406 (1998) 294
Evans, J.W., see Zhang 406 (1998) 178
Evans, M.M.R., J.C. Glueckstein and J. Nogami, Indium on Si(001): growth beyond the first atomic layer 406 (1998) 246

Fernandez, V., see Gießel 406 (1998) 90

Gao, J.N., see Zhao 406 (1998) L614
Gao, J.N., see Yang 406 (1998) 229
Gautier, C., see Breton 406 (1998) 63
Gießel, T., O. Schaff, C.J. Hirschmugl, V. Fernandez, K.-M. Schindler, A. Theobald, S. Bao, R. Lindsay, W. Berndt, A.M. Bradshaw, C. Baddeley, A.F. Lee, R.M. Lambert and

D.P. Woodruff, A photoelectron diffraction study of ordered structures in the chemisorption system Pd{111}-CO 406 (1998) 90
Gillis, H.P., see Winningham 406 (1998) 221
Glebov, A., see Benedek 406 (1998) L621
Glueckstein, J.C., see Evans 406 (1998) 246
Guo, L.W., Q. Huang, Y.K. Li, S.L. Ma, C.S. Peng and J.M. Zhou, Critical Ge concentration for $2 \times n$ reconstruction appearing on GeSi covered Si(100) 406 (1998) L592

Hecht, T., H. Winter and A.G. Borisov, Auger transition rates for the neutralization of $He^+$ ions in front of an aluminium surface 406 (1998) L607
Hirschmugl, C.J., see Gießel 406 (1998) 90
Horley, G., see Mulcahy 406 (1998) 294
Huang, Q., see Guo 406 (1998) L592

Jenks, C.J., see Zhang 406 (1998) 178
Jones, A.C., see Mulcahy 406 (1998) 294
Jones, T.S., see Mulcahy 406 (1998) 294

Kampshoff, E., N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part I: Crystalline and amorphous silicide growth at the Pd(110) surface 406 (1998) 103
Kampshoff, E., N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part II: Amorphous silicide growth at the Pd(100) surface 406 (1998) 117
Kanayama, T., see Tanaka 406 (1998) L603
Kasaya, M., H. Tabata and T. Kawai, Scanning tunneling microscopy and molecular orbital calculation of organic molecules adsorbed on the Si(100)$2 \times 1$ surface 406 (1998) 302
Kawai, T., see Kasaya 406 (1998) 302
Kern, K., see Kampshoff 406 (1998) 103
Kern, K., see Kampshoff 406 (1998) 117
Kosobukin, V.A., Magneto-optics via the near field 406 (1998) 32

Lambert, R.M., see Gießel 406 (1998) 90
Larese, J.Z., see Asmussen 406 (1998) 138
Lee, A.F., see Gießel 406 (1998) 90
Li, X.Q., see Cai 406 (1998) 9
Li, Y.K., see Guo 406 (1998) L592
Lin, J.-C., see Su 406 (1998) 149
Lindsay, R., see Gießel 406 (1998) 90
Liu, F.M., see Cai 406 (1998) 9

Ma, S.L., see Guo 406 (1998) L592
Maa, J.-R., see Chen 406 (1998) 167
Martin, K.P., see Winningham 406 (1998) 221
Miki, K., K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312
Mochán, W.L., see Vargas 406 (1998) L619
Moore, J.T., see Winningham 406 (1998) 221
Motta, N., A. Sgarlata, R. Calarco, Q. Nguyen, J. Castro Cal, F. Patella, A. Balzarotti and M. De Crescenzi, Growth of Ge–Si(111) epitaxial layers: intermixing, strain relaxation and island formation 406 (1998) 254
Mulcahy, C.P.A., J. Eggeling, G. Horley, A.C. Jones, P. O'Brien and T.S. Jones, Vibrational HREELS study of tris-neopentylgallium adsorbed on GaAs(100); identification of surface species and electron excitation mechanisms 406 (1998) 294

Nakabayashi, S., see Yagi 406 (1998) 1
Nguyen, Q., see Motta 406 (1998) 254
Nogami, J., see Evans 406 (1998) 246
Nouaoura, M., see Breton 406 (1998) 63

O'Brien, P., see Mulcahy 406 (1998) 294
O'Connor, D.J., see Shen 406 (1998) 23
Otto, A., see Pohl 406 (1998) 125

Pang, S.J., see Zhao 406 (1998) L614
Pang, S.J., see Yang 406 (1998) 229
Patella, F., see Motta 406 (1998) 254
Peng, C.S., see Guo 406 (1998) L592
Persson, C., see Carlsson 406 (1998) 48
Pohl, M. and A. Otto, Adsorption and reaction of carbon dioxide on pure and alkali-metal promoted cold-deposited copper films 406 (1998) 125
Press, W., see Asmussen 406 (1998) 138

Reijme, M.A., see Ceelen 406 (1998) 264
Ren, B., see Cai 406 (1998) 9
Ribes, V., see Breton 406 (1998) 63
Roberts, M.W., see Carley 406 (1998) L587

Sakamoto, K., see Miki 406 (1998) 312
Sakamoto, T., see Miki 406 (1998) 312
Santra, A.K., see Carley 406 (1998) L587
Schaff, O., see Gießel 406 (1998) 90
Schindler, K.-M., see Gießel 406 (1998) 90
Seifert, W., see Carlsson 406 (1998) 48
Sgarlata, A., see Motta 406 (1998) 254
She, C.X., see Cai 406 (1998) 9
Shen, Y.G., D.J. O'Connor and K. Wandelt, Composition and structure of $Cu_3Pt(001)$: a $(1 \times 1)$ Cu termination with $c(2 \times 2)$ underlayer ordering 406 (1998) 23
Silvestri, W., see Benedek 406 (1998) L621
Skofronick, J.G., see Benedek 406 (1998) L621
Spolveri, I., see Ceelen 406 (1998) 264
Strzelczyk, M., see Asmussen 406 (1998) 138
Su, C. and J.-C. Lin, Thermal desorption of hydrogen from the diamond C(100) surface 406 (1998) 149
Szulczewski, G.J. and J.M. White, Infrared spectroscopy and photodesorption of condensed phase ammonia 406 (1998) 194

Tabata, H., see Kasaya 406 (1998) 302
Tanaka, H. and T. Kanayama, Low-temperature desorption of Si clusters from a graphite surface stabilized by Si desorption 406 (1998) L603

Theobald, A., see Gießel 406 (1998) 90
Thiel, P.A., see Zhang 406 (1998) 178
Thomann, A.-L., see Brault 406 (1998) L597
Thomas, K.K., see Carley 406 (1998) L587
Tian, Z.Q., see Cai 406 (1998) 9
Toennies, J.P., see Benedek 406 (1998) L621

Uosaki, K., see Yagi 406 (1998) 1

Vargas, M.C. and W.L. Mochán, Comment on: "Evidence for a deep bound-state level in the $^4$He–NaCl(001) potential" by G. Benedek, A. Glebov, W. Silvestri, J.G. Skofronick, J.P. Toennies [Surf. Sci. 381 (1997) L540] 406 (1998) L619

Wälchli, N., see Kampshoff 406 (1998) 103
Wälchli, N., see Kampshoff 406 (1998) 117
Wallenberg, L.R., see Carlsson 406 (1998) 48
Wandelt, K., see Shen 406 (1998) 23
Wen, J.-M., see Zhang 406 (1998) 178
White, J.M., see Szulczewski 406 (1998) 194
Winningham, T.A., H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221
Winter, H., see Hecht 406 (1998) L607
Woodruff, D.P., see Gießel 406 (1998) 90

Xue, Z.Q., see Zhao 406 (1998) L614
Xue, Z.Q., see Yang 406 (1998) 229

Yagi, I., S. Nakabayashi and K. Uosaki, Real time monitoring of electrochemical deposition of tellurium on Au(111) electrode by optical second harmonic generation technique 406 (1998) 1
Yakovkin, I.N., Metallization of the monolayer Mg film with a linear atomic structure 406 (1998) 57
Yang, H.Q., see Zhao 406 (1998) L614
Yang, H.Q., J.N. Gao, Y.F. Zhao, Z.Q. Xue and S.J. Pang, Regular defects on the Si(111)-(7 × 7) surface studied by scanning tunneling microscopy 406 (1998) 229
Yang, Y.-M., see Chen 406 (1998) 167
Yoshihara, J., J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

Zhang, C.-M., M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178
Zhao, Y.F., H.Q. Yang, J.N. Gao, Z.Q. Xue and S.J. Pang, Site-specific binding energy terms on Si(111)-7 × 7 surface. A reflection of local binding behavior of surface atoms 406 (1998) L614
Zhao, Y.F., see Yang 406 (1998) 229
Zhou, J.M., see Guo 406 (1998) L592

ELSEVIER

Surface Science 406 (1998) 332–336

surface science

# Subject index

## THEORETICAL METHODS, MODELS AND TECHNIQUES

### Ab initio quantum chemical methods and calculations

A. Allouche, Water adsorption on NaCl(100): a quantum ab-initio cluster calculation 406 (1998) 279

### Atom–solid interactions, scattering, diffraction

T. Hecht, H. Winter and A.G. Borisov, Auger transition rates for the neutralization of $He^+$ ions in front of an aluminium surface 406 (1998) L607

M.C. Vargas and W.L. Mochán, Comment on: "Evidence for a deep bound-state level in the $^4$He–NaCl(001) potential" by G. Benedek, A. Glebov, W. Silvestri, J.G. Skofronick, J.P. Toennies [Surf. Sci. 381 (1997) L540] 406 (1998) L619

### Density functional calculations

I.N. Yakovkin, Metallization of the monolayer Mg film with a linear atomic structure 406 (1998) 57

### Green's function methods

V.A. Kosobukin, Magneto-optics via the near field 406 (1998) 32

### Ion–solid interactions, scattering, channeling

T. Hecht, H. Winter and A.G. Borisov, Auger transition rates for the neutralization of $He^+$ ions in front of an aluminium surface 406 (1998) L607

### Models of surface kinetics

P. Brault, A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597

### Semi-empirical models and model calculations

Y.F. Zhao, H.Q. Yang, J.N. Gao, Z.Q. Xue and S.J. Pang, Site-specific binding energy terms on Si(111)-7 × 7 surface. A reflection of local binding behavior of surface atoms 406 (1998) L614

M. Kasaya, H. Tabata and T. Kawai, Scanning tunneling microscopy and molecular orbital calculation of organic molecules adsorbed on the Si(100)2 × 1 surface 406 (1998) 302

## EXPERIMENTAL SAMPLE PREPARATION AND CHARACTERIZATION METHODS

### Atom–solid reactions

P. Brault, A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597

H. Tanaka and T. Kanayama, Low-temperature desorption of Si clusters from a graphite surface stabilized by Si desorption 406 (1998) L603

### Atom–solid scattering and diffraction – inelastic

T. Hecht, H. Winter and A.G. Borisov, Auger transition rates for the neutralization of $He^+$ ions in front of an aluminium surface 406 (1998) L607

### Atomic force microscopy

W.B. Cai, B. Ren, X.Q. Li, C.X. She, F.M. Liu, X.W. Cai and Z.Q. Tian, Investigation of surface-enhanced Raman scattering from platinum electrodes using a confocal Raman microscope: dependence of surface roughening pretreatment 406 (1998) 9

G. Breton, M. Nouaoura, C. Gautier, M. Cambon, S. Charar, M. Averous and V. Ribes, Annealing under vacuum and Se flux of $CaF_2$ molecular beam epitaxy surfaces prior to PbSe/$CaF_2$/Si growth 406 (1998) 63

T.A. Winningham, H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221

### Auger electron spectroscopy

G. Breton, M. Nouaoura, C. Gautier, M. Cambon, S. Charar, M. Averous and V. Ribes, Annealing under vacuum and Se flux of $CaF_2$ molecular beam epitaxy surfaces prior to PbSe/$CaF_2$/Si growth 406 (1998) 63

W.C.A.N. Ceelen, A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264

**Desorption induced by electronic transitions (DIET)**

***Photon stimulated desorption (PSD)***

G.J. Szulczewski and J.M. White, Infrared spectroscopy and photodesorption of condensed phase ammonia 406 (1998) 194

**Electron emission measurements**

***Photoemission (total yield)***

M. Pohl and A. Otto, Adsorption and reaction of carbon dioxide on pure and alkali-metal promoted cold-deposited copper films 406 (1998) 125

**Electron energy loss spectroscopy**

C.P.A. Mulcahy, J. Eggeling, G. Horley, A.C. Jones, P. O'Brien and T.S. Jones, Vibrational HREELS study of tris-neopentylgallium adsorbed on GaAs(100); identification of surface species and electron excitation mechanisms 406 (1998) 294

**Electron microscopy**

A. Carlsson, L.R. Wallenberg, C. Persson and W. Seifert, Strain state in semiconductor quantum dots on surfaces: a comparison of electron microscopy and finite element calculations 406 (1998) 48

***Scanning transmission electron microscopy (STEM)***

P. Brault, A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597

**Electron–solid diffraction**

***Low energy electron diffraction (LEED)***

W.C.A.N. Ceelen, A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264

***Photoelectron diffraction***

T. Gießel, O. Schaff, C.J. Hirschmugl, V. Fernandez, K.-M. Schindler, A. Theobald, S. Bao, R. Lindsay, W. Berndt, A.M. Bradshaw, C. Baddeley, A.F. Lee, R.M. Lambert and D.P. Woodruff, A photoelectron diffraction study of ordered structures in the chemisorption system Pd{111}-CO 406 (1998) 90

***Reflection high-energy electron diffraction (RHEED)***

L.W. Guo, Q. Huang, Y.K. Li, S.L. Ma, C.S. Peng and J.M. Zhou, Critical Ge concentration for $2 \times n$ reconstruction appearing on GeSi covered Si(100) 406 (1998) L592

G. Breton, M. Nouaoura, C. Gautier, M. Cambon, S. Charar, M. Averous and V. Ribes, Annealing under vacuum and Se flux of $CaF_2$ molecular beam epitaxy surfaces prior to PbSe/$CaF_2$/Si growth 406 (1998) 63

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Ion scattering spectroscopy**

***Low energy ion scattering (LEIS)***

T. Hecht, H. Winter and A.G. Borisov, Auger transition rates for the neutralization of $He^+$ ions in front of an aluminium surface 406 (1998) L607

Y.G. Shen, D.J. O'Connor and K. Wandelt, Composition and structure of $Cu_3Pt(001)$: a $(1 \times 1)$ Cu termination with $c(2 \times 2)$ underlayer ordering 406 (1998) 23

J. Yoshihara, J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

W.C.A.N. Ceelen, A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264

**Molecular beam epitaxy**

G. Breton, M. Nouaoura, C. Gautier, M. Cambon, S. Charar, M. Averous and V. Ribes, Annealing under vacuum and Se flux of $CaF_2$ molecular beam epitaxy surfaces prior to PbSe/$CaF_2$/Si growth 406 (1998) 63

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Neutron scattering**

B. Asmussen, M. Strzelczyk, W. Press and J.Z. Larese, Low coverage structure of tetramethyltin adsorbed on graphite 406 (1998) 138

**Non-linear optical methods**

***Second harmonic generation***

I. Yagi, S. Nakabayashi and K. Uosaki, Real time monitoring of electrochemical deposition of tellurium on Au(111) electrode by optical second harmonic generation technique 406 (1998) 1

**Photon absorption spectroscopy**

***Infrared absorption spectroscopy***

E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part I: Crystalline and amorphous silicide growth at the Pd(110) surface 406 (1998) 103

E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part II: Amorphous silicide growth at the Pd(100) surface 406 (1998) 117

G.J. Szulczewski and J.M. White, Infrared spectroscopy and photodesorption of condensed phase ammonia 406 (1998) 194

**Photon stimulated desorption (non-electronic)**

G.J. Szulczewski and J.M. White, Infrared spectroscopy and photodesorption of condensed phase ammonia 406 (1998) 194

**Raman scattering spectroscopy**

W.B. Cai, B. Ren, X.Q. Li, C.X. She, F.M. Liu, X.W. Cai and Z.Q. Tian, Investigation of surface-enhanced Raman scattering from platinum electrodes using a confocal Raman microscope: dependence of surface roughening pretreatment 406 (1998) 9

M. Pohl and A. Otto, Adsorption and reaction of carbon dioxide on pure and alkali-metal promoted cold-deposited copper films 406 (1998) 125

**Scanning tunneling microscopy**

E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part I: Crystalline and amorphous silicide growth at the Pd(110) surface 406 (1998) 103

E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part II: Amorphous silicide growth at the Pd(100) surface 406 (1998) 117

C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178

H.Q. Yang, J.N. Gao, Y.F. Zhao, Z.Q. Xue and S.J. Pang, Regular defects on the Si(111)-(7 × 7) surface studied by scanning tunneling microscopy 406 (1998) 229

M.M.R. Evans, J.C. Glueckstein and J. Nogami, Indium on Si(001): growth beyond the first atomic layer 406 (1998) 246

M. Kasaya, H. Tabata and T. Kawai, Scanning tunneling microscopy and molecular orbital calculation of organic molecules adsorbed on the Si(100)2 × 1 surface 406 (1998) 302

**Secondary ion mass spectroscopy**

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**X-ray scattering, diffraction, and reflection**

B. Asmussen, M. Strzelczyk, W. Press and J.Z. Larese, Low coverage structure of tetramethyltin adsorbed on graphite 406 (1998) 138

**PHENOMENA**

**Adhesion**

Y.F. Zhao, H.Q. Yang, J.N. Gao, Z.Q. Xue and S.J. Pang, Site-specific binding energy terms on Si(111)-7 × 7 surface. A reflection of local binding behavior of surface atoms 406 (1998) L614

**Adsorption kinetics**

H. Tanaka and T. Kanayama, Low-temperature desorption of Si clusters from a graphite surface stabilized by Si desorption 406 (1998) L603

M. Kasaya, H. Tabata and T. Kawai, Scanning tunneling microscopy and molecular orbital calculation of organic molecules adsorbed on the Si(100)2 × 1 surface 406 (1998) 302

**Atom–solid interactions**

M.C. Vargas and W.L. Mochán, Comment on: "Evidence for a deep bound-state level in the $^4$He–NaCl(001) potential" by G. Benedek, A. Glebov, W. Silvestri, J.G. Skofronick, J.P. Toennies [Surf. Sci. 381 (1997) L540] 406 (1998) L619

**Catalysis**

M. Pohl and A. Otto, Adsorption and reaction of carbon dioxide on pure and alkali-metal promoted cold-deposited copper films 406 (1998) 125

J. Yoshihara, J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

**Chemisorption**

A.F. Carley, P.R. Davies, M.W. Roberts, A.K. Santra and K.K. Thomas, Coadsorption of carbon monoxide and nitric oxide at Ag(111): evidence for a CO–NO surface complex 406 (1998) L587

T. Gießel, O. Schaff, C.J. Hirschmugl, V. Fernandez, K.-M. Schindler, A. Theobald, S. Bao, R. Lindsay, W. Berndt, A.M. Bradshaw, C. Baddeley, A.F. Lee, R.M. Lambert and D.P. Woodruff, A photoelectron diffraction study of ordered structures in the chemisorption system Pd{111}-CO 406 (1998) 90

J. Yoshihara, J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Diffusion and migration**

P. Brault, A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597

**Epitaxy**

A. Carlsson, L.R. Wallenberg, C. Persson and W. Seifert, Strain state in semiconductor quantum dots on surfaces: a comparison of electron microscopy and finite element calculations 406 (1998) 48

A. Barbier, Generalized model for interface description 406 (1998) 69

C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178

J. Yoshihara, J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

N. Motta, A. Sgarlata, R. Calarco, Q. Nguyen, J. Castro Cal, F. Patella, A. Balzarotti and M. De Crescenzi, Growth of

Ge–Si(111) epitaxial layers: intermixing, strain, relaxation and island formation 406 (1998) 254
C.P.A. Mulcahy, J. Eggeling, G. Horley, A.C. Jones, P. O'Brien and T.S. Jones, Vibrational HREELS study of tris-neopentylgallium adsorbed on GaAs(100); identification of surface species and electron excitation mechanisms 406 (1998) 294

**Etching**

T.A. Winningham, H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221

**Evaporation and sublimation**

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Faceting**

A. Barbier, Generalized model for interface description 406 (1998) 69

**Growth**

P. Brault, A.-L. Thomann and C. Andreazza-Vignolle, Percolative growth of palladium ultrathin films deposited by plasma sputtering 406 (1998) L597
I. Yagi, S. Nakabayashi and K. Uosaki, Real time monitoring of electrochemical deposition of tellurium on Au(111) electrode by optical second harmonic generation technique 406 (1998) 1
A. Carlsson, L.R. Wallenberg, C. Persson and W. Seifert, Strain state in semiconductor quantum dots on surfaces: a comparison of electron microscopy and finite element calculations 406 (1998) 48
A. Barbier, Generalized model for interface description 406 (1998) 69
E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part I: Crystalline and amorphous silicide growth at the Pd(110) surface 406 (1998) 103
E. Kampshoff, N. Wälchli and K. Kern, Silicide formation at palladium surfaces. Part II: Amorphous silicide growth at the Pd(100) surface 406 (1998) 117
C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178
M.M.R. Evans, J.C. Glueckstein and J. Nogami, Indium on Si(001): growth beyond the first atomic layer 406 (1998) 246

**Light scattering**

V.A. Kosobukin, Magneto-optics via the near field 406 (1998) 32

**Nucleation**

C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178
T.A. Winningham, H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221

**Photoelectron emission**

I.N. Yakovkin, Metallization of the monolayer Mg film with a linear atomic structure 406 (1998) 57

**Physical adsorption**

B. Asmussen, M. Strzelczyk, W. Press and J.Z. Larese, Low coverage structure of tetramethyltin adsorbed on graphite 406 (1998) 138
A. Allouche, Water adsorption on NaCl(100): a quantum ab-initio cluster calculation 406 (1998) 279

**Self-assembly**

A. Carlsson, L.R. Wallenberg, C. Persson and W. Seifert, Strain state in semiconductor quantum dots on surfaces: a comparison of electron microscopy and finite element calculations 406 (1998) 48
T.A. Winningham, H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221

**Sticking**

H. Tanaka and T. Kanayama, Low-temperature desorption of Si clusters from a graphite surface stabilized by Si desorption 406 (1998) L603

**Surface diffusion**

C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178
T.A. Winningham, H.P. Gillis, D.A. Choutov, K.P. Martin, J.T. Moore and K. Douglas, Formation of ordered nanocluster arrays by self-assembly on nanopatterned Si(100) surfaces 406 (1998) 221

**Surface electronic phenomena (work function, surface potential, surface states, etc.)**

I.N. Yakovkin, Metallization of the monolayer Mg film with a linear atomic structure 406 (1998) 57
J. Yoshihara, J.M. Campbell and C.T. Campbell, Cu films on a Zn-terminated ZnO(0001) surface: structure and electronic properties 406 (1998) 235

**Surface relaxation and reconstruction**

L.W. Guo, Q. Huang, Y.K. Li, S.L. Ma, C.S. Peng and J.M. Zhou, Critical Ge concentration for $2 \times n$ reconstruction appearing on GeSi covered Si(100) 406 (1998) L592
K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Surface roughening**

W.B. Cai, B. Ren, X.Q. Li, C.X. She, F.M. Liu, X.W. Cai and Z.Q. Tian, Investigation of surface-enhanced Raman scattering from platinum electrodes using a confocal Raman microscope: dependence of surface roughening pretreatment 406 (1998) 9

C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel, Submonolayer island formation and the onset of multilayer growth during Ag/Ag(100) homoepitaxy 406 (1998) 178

**Surface segregation**

L.W. Guo, Q. Huang, Y.K. Li, S.L. Ma, C.S. Peng and J.M. Zhou, Critical Ge concentration for $2 \times n$ reconstruction appearing on GeSi covered Si(100) 406 (1998) L592

Y.G. Shen, D.J. O'Connor and K. Wandelt, Composition and structure of $Cu_3Pt(001)$: a $(1 \times 1)$ Cu termination with $c(2 \times 2)$ underlayer ordering 406 (1998) 23

W.C.A.N. Ceelen, A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264

**Surface structure, morphology, roughness, and topography**

Y.G. Shen, D.J. O'Connor and K. Wandelt, Composition and structure of $Cu_3Pt(001)$: a $(1 \times 1)$ Cu termination with $c(2 \times 2)$ underlayer ordering 406 (1998) 23

T. Gießel, O. Schaff, C.J. Hirschmugl, V. Fernandez, K.-M. Schindler, A. Theobald, S. Bao, R. Lindsay, W. Berndt, A.M. Bradshaw, C. Baddeley, A.F. Lee, R.M. Lambert and D.P. Woodruff, A photoelectron diffraction study of ordered structures in the chemisorption system Pd{111}-CO 406 (1998) 90

B. Asmussen, M. Strzelczyk, W. Press and J.Z. Larese, Low coverage structure of tetramethyltin adsorbed on graphite 406 (1998) 138

P. Dooley and S.L. Bernasek, Pooling analysis of scanning probe microscopy images 406 (1998) 206

M.M.R. Evans, J.C. Glueckstein and J. Nogami, Indium on Si(001): growth beyond the first atomic layer 406 (1998) 246

W.C.A.N. Ceelen, A.W. Denier van der Gon, M.A. Reijme, H.H. Brongersma, I. Spolveri, A. Atrei and U. Bardi, Domain structure, segregation and morphology of the $Pt_3Sn(111)$ surface 406 (1998) 264

K. Miki, K. Sakamoto and T. Sakamoto, Surface preparation of Si substrates for epitaxial growth 406 (1998) 312

**Surface waves**

***Plasmons***

V.A. Kosobukin, Magneto-optics via the near field 406 (1998) 32

**Thermal desorption**

H. Tanaka and T. Kanayama, Low-temperature desorption of Si clusters from a graphite surface stabilized by Si desorption 406 (1998) L603

C. Su and J.-C. Lin, Thermal desorption of hydrogen from the diamond C(100) surface 406 (1998) 149

**Tunneling**

M. Kasaya, H. Tabata and T. Kawai, Scanning tunneling microscopy and molecular orbital calculation of organic molecules adsorbed on the Si(100)2 × 1 surface 406 (1998) 302